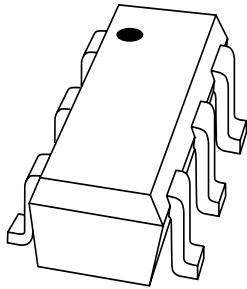


DATA SHEET



BC857BS

PNP general purpose double
transistor

Product data sheet
Supersedes data of 1997 Jul 09

1999 Apr 26

PNP general purpose double transistor

BC857BS

FEATURES

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and boardspace
- No mutual interference between the transistors.

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

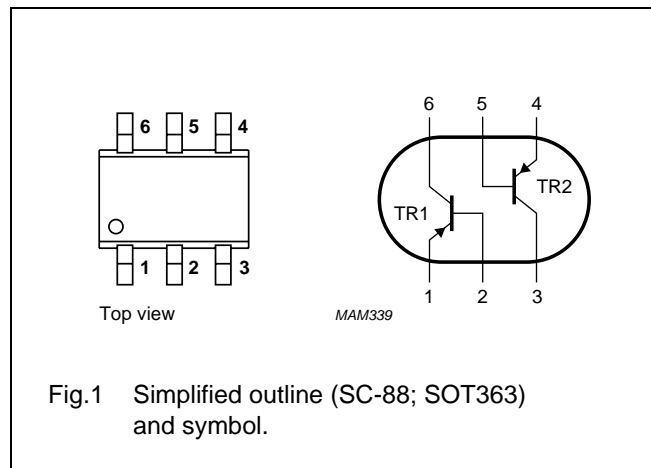
PNP double transistor in an SC-88; SOT363 plastic package. NPN complement: BC847BS.

MARKING

TYPE NUMBER	MARKING CODE
BC857BS	3Ft

PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor					
V_{CBO}	collector-base voltage	open emitter	–	–50	V
V_{CEO}	collector-emitter voltage	open base	–	–45	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–200	mA
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C
Per device					
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	300	mW

Note

1. Device mounted on an FR4 printed-circuit board.

PNP general purpose double transistor

BC857BS

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per device				
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	416	K/W

Note

1. Device mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

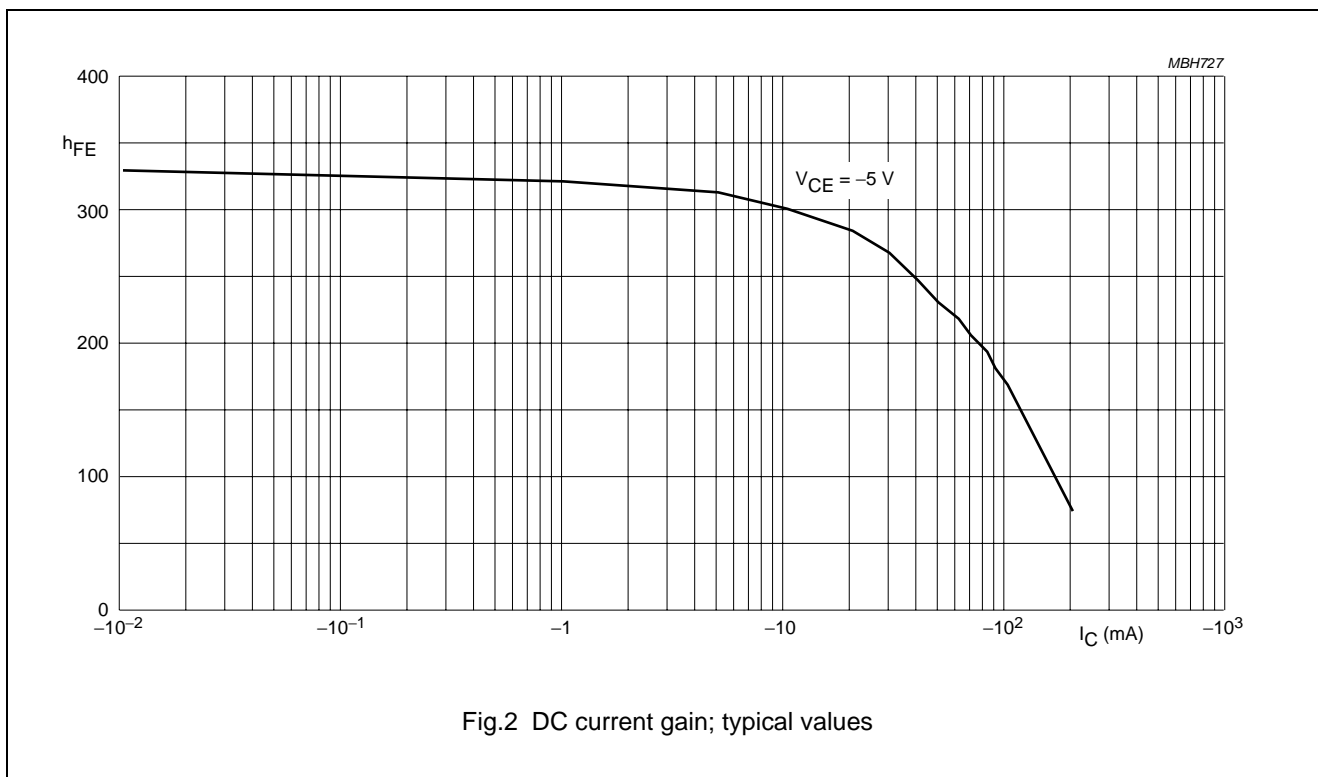
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transistor						
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	-	-	-15	nA
		$I_E = 0; V_{CB} = -30\text{ V}; T_j = 150\text{ °C}$	-	-	-5	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	-	-	-100	nA
h_{FE}	DC current gain	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	200	-	450	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	-	-	-100	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA}; \text{note 1}$	-	-	-400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	-	-755	-	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = -5\text{ V}$	-600	-655	-750	mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	-	-	2.2	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = -500\text{ mV}; f = 1\text{ MHz}$	-	10	-	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	-	-	MHz

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

PNP general purpose double transistor

BC857BS



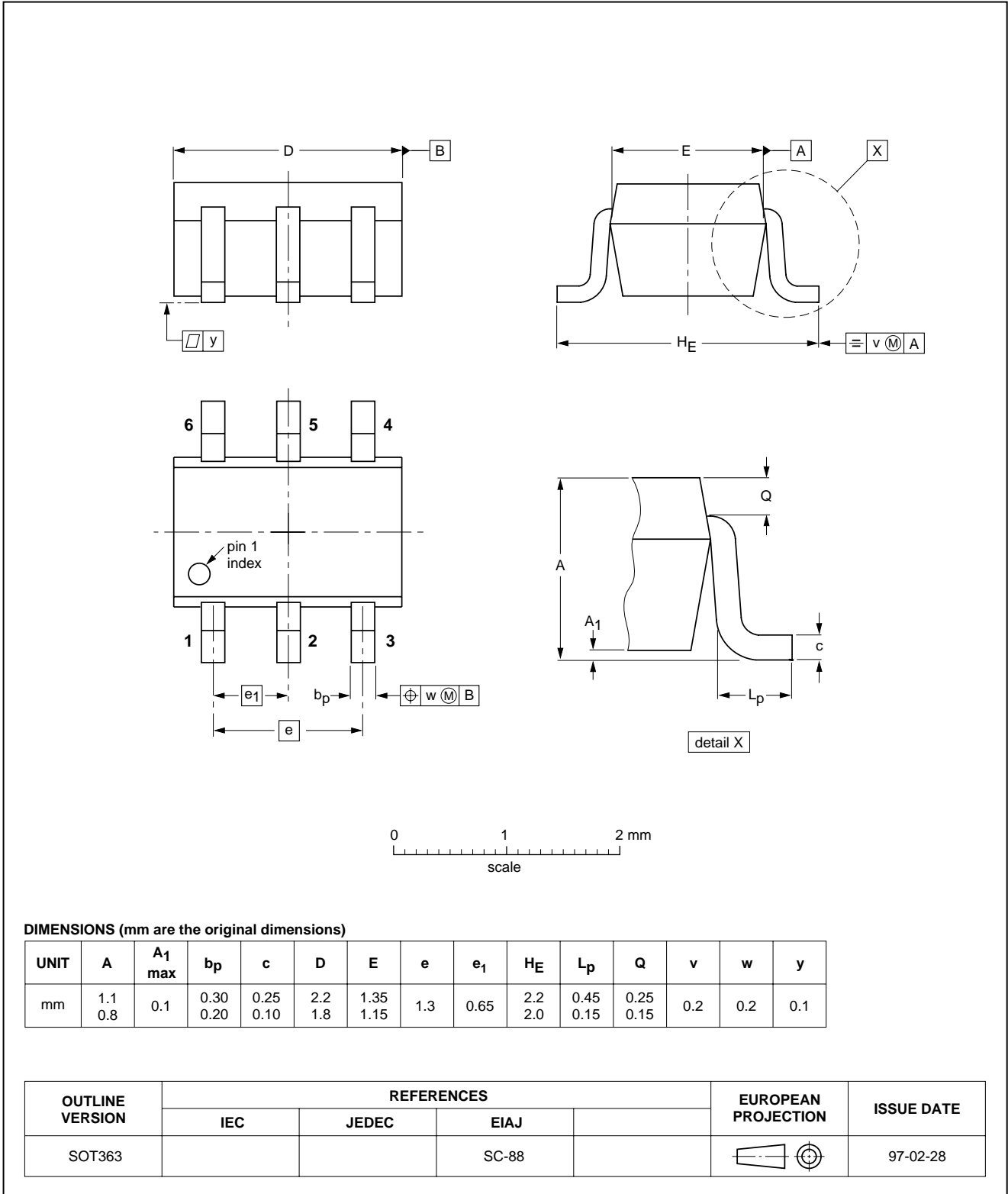
PNP general purpose double transistor

BC857BS

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



PNP general purpose double transistor

BC857BS

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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